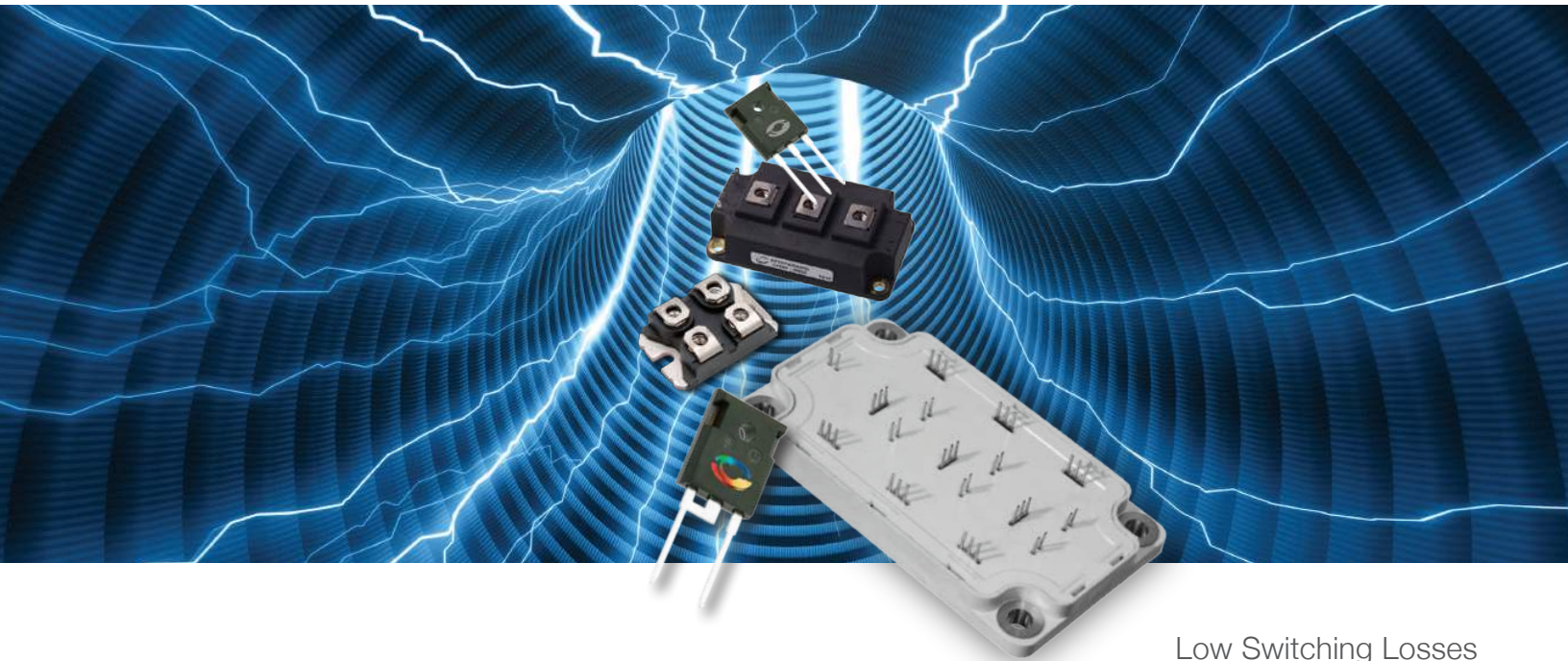


Silicon Carbide Semiconductor Products



Low Switching Losses

Low Gate Resistance

High Power Density

High Thermal Conductivity

High Avalanche (UIS) Rating

Reduced Heat Sink Requirements

High Temperature Operation

Reduced Circuit Size and System Costs

Overview

Silicon Carbide (SiC) is the ideal technology for higher switching frequency, higher efficiency, and higher power (>650 V) applications. Target markets and applications include:

- Commercial aviation—actuation, air conditioning, power distribution
- Industrial—motor drives, welding, UPS, SMPS, induction heating
- Transportation/automotive—EV battery charger, onboard chargers, H/EV powertrain, DC-DC converter, energy recovery
- Smart energy—PV inverter, wind turbine
- Medical—MRI power supply, X-Ray power supply
- Defense and oil drilling—motor drives, auxiliary power supplies

SiC MOSFET and SiC Schottky Barrier Diode product lines from Microsemi increase your system efficiency over silicon MOSFET and IGBT solutions while lowering your total cost of ownership by enabling downsized systems and smaller/lower cost cooling.

Full In-House and Foundry Capabilities

Design

- Silvaco design and process simulator
- TCAD-TMA
- Mask-making and layout
- Solid works and FEA

Process

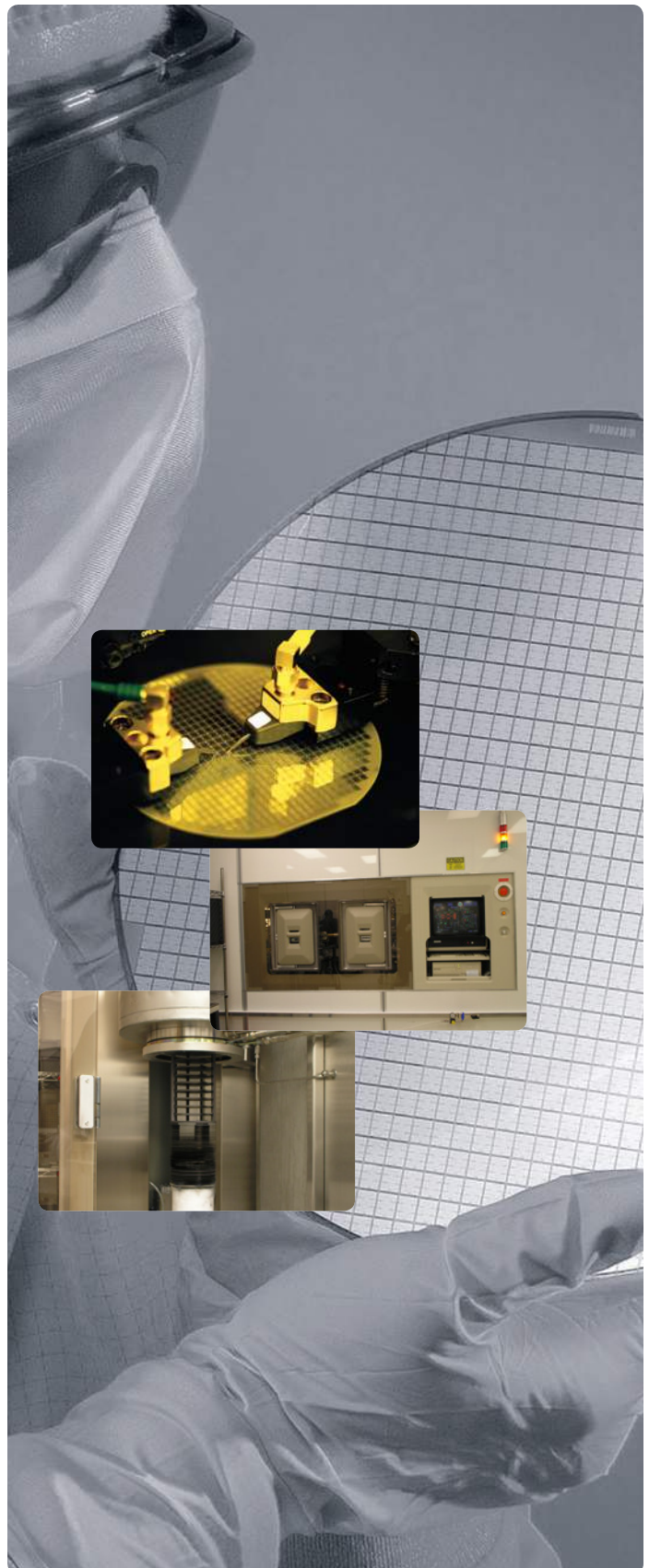
- High-temperature ion implantation
- High-temperature annealing
- SiC MOSFET gate oxide
- ASML steppers
- RIE and plasma etching
- Sputtered and evaporated metal deposition

Analytical and Support

- SEM/EDAX
- Thermal imaging
- Photo Emission Microscope system (Phemos 1000)

Reliability Testing and Screening

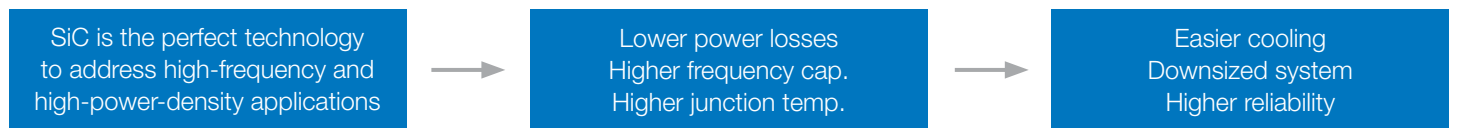
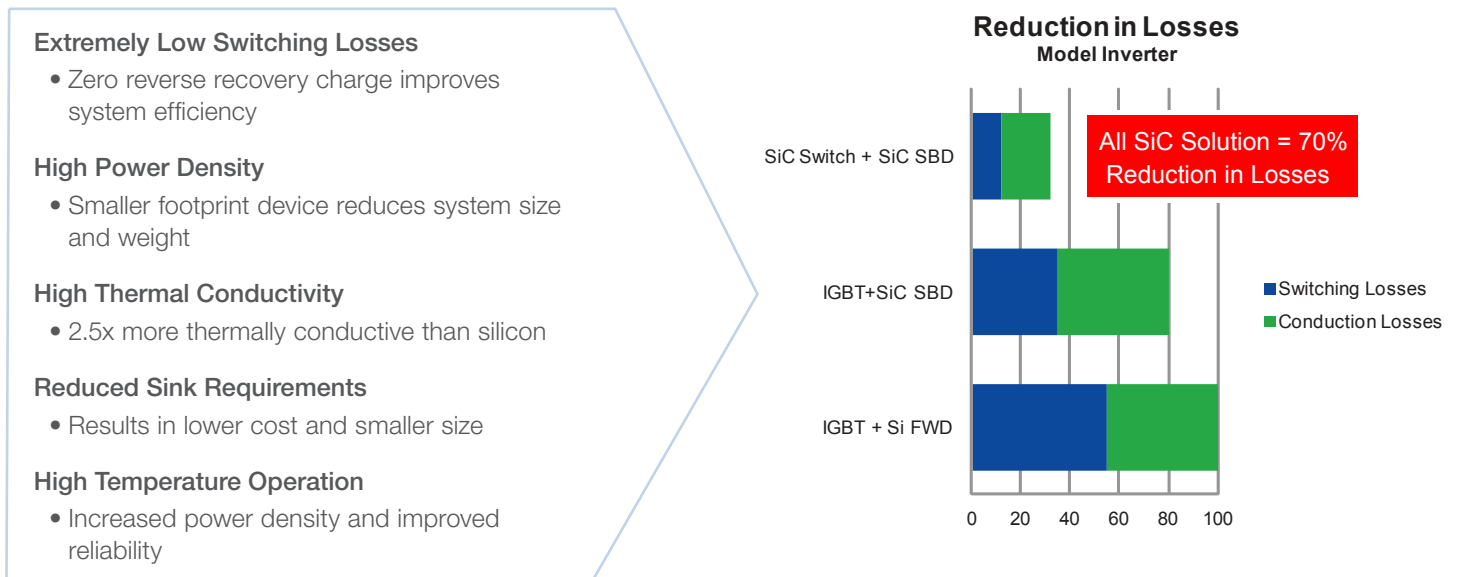
- AEC-Q101
- Wafer-level HTRB/HTGB
- Sonoscan and X-ray



The Power of Silicon Carbide Semiconductors

Breakthrough Technology Combines High Performance with Low Losses

Silicon Carbide (SiC) semiconductors are an innovative new option for power electronic designers looking to improve system efficiency, with a smaller form factor and higher operating temperature in products covering industrial, automotive, medical, mil-aerospace, and communication market segments. Microsemi is proud to be at the forefront of this game changing technology with a comprehensive portfolio of SiC solutions.



Power Modules

SiC Power Module Advantages

- High-speed switching
- Low input capacitance
- Low profile
- Lower system cost
- Low switching losses
- Low drive requirements
- Minimum parasitic inductance
- Increased reliability

Standard Modules

Part Number	Type	Electrical Topology	Voltage (V)	Current (A)	Package Type	
APT2X20DC60J	Diode module	Dual diode	600	20	SOT227	
APT2X30DC60J				30	SOT227	
APT2X40DC60J				40	SOT227	
APT2X50DC60J				50	SOT227	
APT2X60DC60J				60	SOT227	
APT2X20DC120J				1200	20	SOT227
APT2X40DC120J		40	SOT227			
APT2X50DC120J		50	SOT227			
APT2X60DC120J		60	SOT227			
APT40DC60HJ		Full bridge	600	40	SOT227	
APTDC40H601G				40	SP1	
APT20DC120HJ				1200	20	SOT227
APTDC20H1201G	20				SP1	
APT40DC120HJ	40				SOT227	
APT30SM120JCU2	Boost chopper				1200	30
APT100MC120JCU2		100	SOT227			
APTSM120HM50CT3AG	Full bridge	1200	59	SP3F		
APTMC120HM17CT3AG			110	SP3F		
APTMC120AM55CT1AG	Phase leg	1200	40	SP1		
APTSM120AM55CT1AG			59	SP1		
APTMC120AM25CT3AG			80	SP3F		
APTMC120AM20CT1AG			100	SP1		
APTSM120AM25CT3AG			118	SP3F		
APTMC120AM12CT3AG			150	SP3F		
APTMC120AM08CD3AG			185	D3		
APTMC120AM09CT3AG			200	SP3F		
APTSM120AM08CT6AG			293	SP6		
APTMC170AM60CT1AG			1700	40	SP1	
APTMC170AM30CT1AG				80	SP1	
APTMC60TL11CT3AG			Three level inverter	600	20	SP3F
APTMC60TLM55CT3AG					40	SP3F
APTMC60TLM14CAG					160	SP6
APTMC120HR11CT3AG	Three phase bridge	1200	20	SP3F		
APTMC120HRM40CT3AG			50	SP3F		
APTSM120TA10CT3AG			30	SP3F		
APTSM120TAM34CT3AG			55	SP3F		
APTSM120TAM33CTPAG	Triple phase leg	1200	89	SP6P		
APTMC120TAM17CTPAG			100	SP6P		
APTMC120TAM12CTPAG			150	SP6P		

Customization

Microsemi offers a complete engineering solution with mix and match capabilities in terms of package, interconnection, configuration, performance, and cost.

Out of the existing standard power modules product line, Microsemi can offer simple, modified, or fully customized parts to meet 100% of our customers' needs.

- Design expertise
- Low profile packages
- Extended temperature capabilities
- Pin locating flexibility
- High power density
- Mix of silicon

Discrete Products

SiC Schottky Barrier Diodes

Part Number	Voltage (V)	I _F (A)	V _F (Typical at 25°C)	Package
MSC010SDA070K	700	10	1.5	TO-220
MSC030SDA070K		30	1.5	TO-220
MSC050SDA070B		50	1.5	TO-247
MSC010SDA120B	1200	10	1.5	TO-247
MSC010SDA120K		10	1.5	TO-220
MSC030SDA120B		30	1.5	TO-247
MSC030SDA120S		30	1.5	D3PAK
MSC050SDA120B		50	1.5	TO-247
MSC050SDA120S		50	1.5	D3PAK
MSC010SDA170B	1700	10	1.5	TO-247
MSC030SDA170B		30	1.5	TO-247
MSC050SDA170B		50	1.5	TO-247

SiC MOSFETs

Part Number	Voltage (V)	Current (A)	R _{DS(ON)} (Typical)	Package
APT35SM70B	700	35	125 mΩ*	TO-247
APT35SM70S				D3PAK
APT70SM70B	700	58	75 mΩ*	TO-247
APT70SM70S				D3PAK
APT70SM70J				SOT-227
APT130SM70B	700	78	35 mΩ*	TO-247
APT130SM70J				SOT-227
APT25SM120B	1200	25	140 mΩ	TO-247
APT25SM120S				D3PAK
APT40SM120B	1200	40	80 mΩ	TO-247
APT40SM120S				D3PAK
APT40SM120J				SOT-227
APT80SM120B	1200	80	40 mΩ	TO-247
APT80SM120S				D3PAK
APT80SM120J				SOT-227

*Preliminary current and typical R_{DS(ON)} values. Consult the datasheet for device ratings by package.

SiC MOSFETs

Characteristics	SiC vs. Si	Results	Benefits
Breakdown field (MV/cm)	10x higher	Lower on-resistance	Higher efficiency
Electron sat. velocity (cm/s)	2x higher	Faster switching	Size reduction
Bandgap energy (ev)	3x higher	Higher junction temperature	Improved cooling
Thermal conductivity (W/m.K)	3x higher	Higher power density	Higher current capabilities
Positive temperature coefficient		Self regulation	Easy paralleling

SiC Modules= Higher Power Density

Parameter	Microsemi APTGLQ300A120G	Microsemi APTMC120AM20CT1AG	Comparison: SiC vs Si
Semiconductor type	Trench4 IGBT	SiC MOSFET	
Ratings at Tc=25°C	500 A/1200 V	143 A/1200 V	
Package type	SP6: 108 mm × 62 mm	SP1: 52 mm × 41 mm	3x smaller
Current at 30 kHz Tc=75°C, D=50%, V=600 V	130 A	130 A	
Current at 50 kHz Tc=75°C, D=50%, V=600 V	60 A	115 A	~2.0x higher
Eon+Eoff at 100 A Tj=150°C, V=600 V	16.0 mJ	3.4 mJ	4.7x lower

Microsemi is continually adding new products to its industry-leading portfolio.

For the most recent updates to our product line and for detailed information and specifications, please call, email, or visit our website.

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